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061005T4ICT ICT TECHNICIAN LEVEL 5 IT/OS/ICT/CC/01/5 APPLY BASIC ELECTRONICS Nov. /Dec. 2022



WRITTEN ASSESSMENT

Time: 3 hours

INSTRUCTIONS TO CANDIDATES

Maximum marks for each question are indicated in brackets. This paper consists of **THREE** sections: **A**, **B** and **C**. Answer questions as per the instructions in each section. You are provided with a separate answer booklet. Answer all the questions in English.

> This paper consists of EIGHT (8) printed pages Candidates should check the question paper to ascertain that all pages are printed as indicated and that no questions are missing

SECTION A (20 MARKS)

(Answer all questions in this section)

| 1. The following are basic logic gates except? | (1 Mark) |
|--|----------|
| A. NAND gate | |
| B. OR gate | |
| C. AND gate | |
| D. NOR gate | |
| 2. A device which converts BCD to seven segments is called? (1 Mark) | |
| A. Encoder | |
| B. Decoder | |
| C. Multiplexer | |
| D. Converter | |
| D. Converter 3. The basic storage element in a digital system is? A. Flip-flop B. Counter C. Multiplexer D. Encoder | (1 Mark) |
| A. Flip-flop | |
| B. Counter | |
| C. Multiplexer | |
| D. Encoder | |
| 4. Which of the following device has one input and many outputs? | (1 Mark) |
| A. Multiplexer | |
| B. Demultiplexer | |
| C. Counter | |
| D. Flip flop | |
| 5. Write 11100110 in 1's complement. | (1 Mark) |
| A. 00011001 | |
| B. 10000001 | |
| C. 00011010 | |
| D. 00000000 | |
| | |

| 6. | The number of depletion layers in a transistor is | (1 Mark) |
|----|--|----------------|
| | A. Four | |
| | B. Three | |
| | C. One | |
| | D. Two | |
| 7. | What carries current is in a PnP transistor? | (1 Mark) |
| | A. Acceptor ions | |
| | B. Donor ions | |
| | C. Free electrons | |
| | D. Holes | |
| 8. | Which oscillator is used in a transmitter? | (1 Mark) |
| | A. Hartley | |
| | B. RC phase-shift | |
| | C. Wien-bridge | |
| | C. Wien-bridge D. Crystal | |
| 9. | If a radio receiver amplifies all the signal frequencies accurately, it is said | d to have high |
| | | (1 Mark) |
| | | (1 Mark) |
| | A. Sensitivity | (1 Wark) |
| | A. SensitivityB. Selectivity | (T Wark) |
| | - | (T Wark) |
| | B. Selectivity | (T Wark) |
| 10 | B. SelectivityC. Distortion | (1 Mark) |
| 10 | B. SelectivityC. DistortionD. Fidelity | |
| 10 | B. Selectivity C. Distortion D. Fidelity The major advantage of FM over AM is | |
| 10 | B. Selectivity C. Distortion D. Fidelity The major advantage of FM over AM is A. Reception is less noisy | |
| 10 | B. Selectivity C. Distortion D. Fidelity The major advantage of FM over AM is A. Reception is less noisy B. Higher carrier frequency | |
| | B. Selectivity C. Distortion D. Fidelity The major advantage of FM over AM is A. Reception is less noisy B. Higher carrier frequency C. Smaller bandwidth | |
| | B. Selectivity C. Distortion D. Fidelity The major advantage of FM over AM is A. Reception is less noisy B. Higher carrier frequency C. Smaller bandwidth D. Small frequency deviation | (1 Mark) |
| | B. Selectivity C. Distortion D. Fidelity The major advantage of FM over AM is A. Reception is less noisy B. Higher carrier frequency C. Smaller bandwidth D. Small frequency deviation The purpose of a parallel circuit resonance is to magnify | (1 Mark) |
| | B. Selectivity C. Distortion D. Fidelity The major advantage of FM over AM is A. Reception is less noisy B. Higher carrier frequency C. Smaller bandwidth D. Small frequency deviation The purpose of a parallel circuit resonance is to magnify A. Current | (1 Mark) |

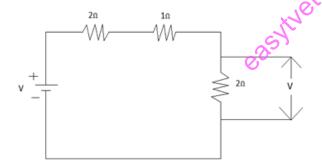
| 12. A semiconductor is formed by bonds. | (1 Mark) |
|---|----------------------|
| A. Covalent | |
| B. Electrovalent | |
| C. Co-ordinate | |
| D. None of the above | |
| 13. Both EPROM and EEPROM are | (1 Mark) |
| A. Sequential access memory | |
| B. Random access memory | |
| C. Volatile memory | |
| D. Destructive memory | |
| 14. Which of the following waves has the highest value of peak factor? | (1 Mark) |
| A. Square wave | |
| B. Sine wave | |
| C. Half wave rectified sine wave | |
| D. Triangular wave | |
| 15. Skin effect occurs when a conductor carries current at frequencies | . (1 Mark) |
| | |
| A. Very low | |
| A. Very low B. Low | |
| | |
| B. Low | |
| B. Low C. Medium | (1 Mark) |
| B. Low C. Medium D. High | (1 Mark) |
| B. Low C. Medium D. High 16. Which of the following refers to a parallel circuit? | (1 Mark) |
| B. Low C. Medium D. High 16. Which of the following refers to a parallel circuit? A. The current through each element is same | (1 Mark) |
| B. Low C. Medium D. High 16. Which of the following refers to a parallel circuit? A. The current through each element is same B. The voltage across element is in appropriate to it's resistance value | (1 Mark) |
| B. Low C. Medium D. High 16. Which of the following refers to a parallel circuit? A. The current through each element is same B. The voltage across element is in appropriate to it's resistance value C. The equivalent resistance is greater than any one of the resistors D. The current through any one element is less than the source current | (1 Mark) (1 Mark) |
| B. Low C. Medium D. High 16. Which of the following refers to a parallel circuit? A. The current through each element is same B. The voltage across element is in appropriate to it's resistance value C. The equivalent resistance is greater than any one of the resistors D. The current through any one element is less than the source current 17. The power factor of a D.C. circuit is always? | |
| B. Low C. Medium D. High 16. Which of the following refers to a parallel circuit? A. The current through each element is same B. The voltage across element is in appropriate to it's resistance value C. The equivalent resistance is greater than any one of the resistors D. The current through any one element is less than the source current 17. The power factor of a D.C. circuit is always? A. Less than unity | |
| B. Low C. Medium D. High 16. Which of the following refers to a parallel circuit? A. The current through each element is same B. The voltage across element is in appropriate to it's resistance value C. The equivalent resistance is greater than any one of the resistors D. The current through any one element is less than the source current 17. The power factor of a D.C. circuit is always? | |

| 18. The active components in an IC are? | (1 Mark) |
|---|----------|
| A. Resistors & Capacitors | |
| B. Capacitors & diodes | |
| C. Transistors and diodes | |
| D. None of the above | |
| 19. Which of the following is the most popular type of IC | (1 Mark) |
| A. Thin-film | |
| B. Hybrid | |
| C. Thick-film | |
| D. Monolithic | |
| 20. Which of the following is most difficult to fabricate in an IC? | (1 Mark) |
| A. Diode | |
| B. Transistor | |
| C. FET | |
| D. Capacitor | |
| - Male | |
| C. FET D. Capacitor | |

SECTION B (40 MARKS)

(Answer all questions in this section)

| 21. a) Differentiate between the following | (2 Marks) |
|--|-----------|
| i) A.C and D.C currents | |
| ii) Electrolyte and Electrode | |
| b) Explain the following as used in electronics. | (8 Marks) |
| i) potential difference | |
| ii) Current | |
| iii) Voltage | |
| iv) Power | |
| 22. a) What is an electric current? | (1 Mark) |
| b) Explain the two types of Electric Circuits | (4 Marks) |
| c) Calculate Voltage across 2 Ω Resistor where supply v= 10volts. | (4 Marks) |



d) If there are 3 Resistors R_1 , R_2 and R_3 in series and V is total voltage and I is total current then Voltage across R_2 is? (1 Mark)

23. Explain any **five** electronic components and their functions. (10 Marks)

- 24. a) Define semiconductor. (2 Marks)
 - b) Explain **two** types of extrinsic semiconductors? (4 Marks)
 - c) With aid of a sketch, outline the PN junction diode showing the flow of current and
 - depletion region formation. (4 Marks)

SECTION C (40 MARKS)

(Answer any two questions in this section)

| 25. a) Define ohm's law. | (2 Marks) |
|--|------------|
| b) State the purpose of fuse and circuit breakers? | (2 Marks) |
| c) Outline any four advantages of semiconductors that make them highly useful in almost | |
| all electronic devices. | (4 Marks) |
| d) Explain the following as used in Bipolar transistor configuration | (6 Marks) |
| i) Common Base Configuration | |
| ii) Common Emitter Configuration | |
| iii) Common Collector Configuration | |
| e) With aid of a sketch, outline the configurations of PN junction diode showing both the | |
| input signal and output. 26. a) Define Capacitance | (6 Marks) |
| 26. a) Define Capacitance | (2 Marks) |
| b) Draw a closed circuit of three inductors (L1, L2 and L3) in series, showing the current (I) | |
| flow and voltage (V1, V2 and V3) across each inductor. | (6 Marks) |
| c) Discuss any six challenges of emerging trends in electronic manufacturing | (12 Marks) |
| 27. a) Convert the following Binary numbers to their decimal equivalent | (8 Marks) |
| i) (1110010) ₂ | |
| ii) (11011) ₂ | |
| b) Convert the following Binary Numbers to octal equivalent | (4 Marks) |
| i) 10101 ₂ | |
| ii) 0110 011.1011 ₂ | |

| c. Convert binary number 1101010 into hexadecimal number. | (6 Marks) |
|---|-----------|
| d. Convert hexadecimal number 1F.01B into decimal number. | (2 Marks) |
| 28. a) Explain the following as used in atomic structure. | (6 Marks) |
| i) Atom | |
| ii) Proton | |
| iii) Neutron | |
| b) What is the difference between the following | (6 Marks) |
| i) Cache memory and virtual memory? | |
| ii) Volatile memory and Non-volatile memory | |
| iii) DRAM and SRAM | |
| c) Discuss four types of Read Only Memory | (8 Marks) |
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